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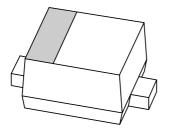
If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

# **DISCRETE SEMICONDUCTORS**

# DATA SHEET



# **PMEG3002AEB**Low V<sub>F</sub> MEGA Schottky barrier diode

Product data sheet

2002 May 06



# Low V<sub>F</sub> MEGA Schottky barrier diode

# PMEG3002AEB

### **FEATURES**

Forward current: 0.2 AReverse voltage: 30 VVery low forward voltage

• Ultra small SMD package.

# **APPLICATIONS**

Ultra high-speed switching

• High efficiency DC/DC conversion

· Voltage clamping

• Inverse-polarity protection

· Low voltage rectification

• Low power consumption applications.

### **DESCRIPTION**

Planar Maximum Efficiency General Application (MEGA) Schottky barrier diode with an integrated guard ring for stress protection, encapsulated in a SOD523 (SC-79) ultra small SMD plastic package.

### **PINNING**

PIN	DESCRIPTION
1	cathode
2	anode

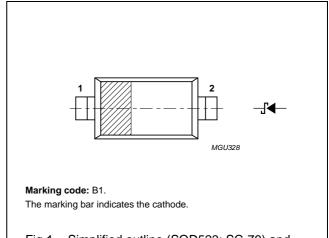


Fig.1 Simplified outline (SOD523; SC-79) and symbol.

### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>R</sub>	continuous reverse voltage		_	30	V
I <sub>F</sub>	continuous forward current		_	200	mA
I <sub>FRM</sub>	repetitive peak forward current	$t_p \le 1 \text{ s}; \ \delta \le 0.5$	_	300	mA
I <sub>FSM</sub>	non-repetitive peak forward current	t <sub>p</sub> = 8.3 ms half sinewave; JEDEC method	_	1	А
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		_	125	°C
T <sub>amb</sub>	operating ambient temperature		-65	+125	°C

# Low V<sub>F</sub> MEGA Schottky barrier diode

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# **ELECTRICAL CHARACTERISTICS**

 $T_{amb}$  = 25 °C; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V <sub>F</sub>	continuous forward voltage	see Fig.2			
		$I_F = 0.1 \text{ mA}$	130	190	mV
		I <sub>F</sub> = 1 mA	190	250	mV
		I <sub>F</sub> = 10 mA	255	300	mV
		I <sub>F</sub> = 100 mA	355	400	mV
		I <sub>F</sub> = 200 mA	420	480	mV
I <sub>R</sub>	continuous reverse current	V <sub>R</sub> = 10 V; see Fig.3; note 1	2.5	10	μΑ
C <sub>d</sub>	diode capacitance	V <sub>R</sub> = 1 V; f = 1 MHz; see Fig.4	20	25	pF

# Note

1. Pulsed test:  $t_p$  = 300  $\mu$ s;  $\delta$  = 0.02.

# THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to	note 1	450	K/W
	ambient			

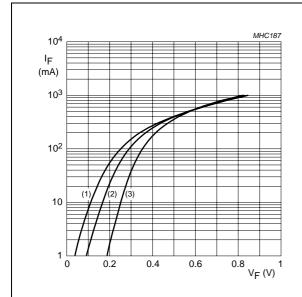
## Note

1. Refer to SOD523 (SC-79) standard mounting conditions.

# Low V<sub>F</sub> MEGA Schottky barrier diode

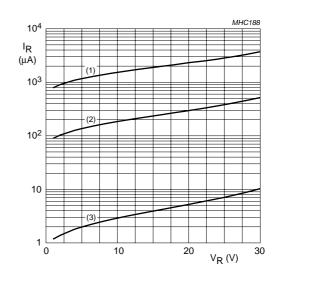
# PMEG3002AEB

# **GRAPHICAL DATA**



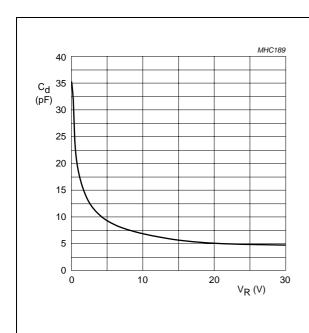
- (1)  $T_{amb} = 125 \, ^{\circ}C$ .
- (2)  $T_{amb} = 85 \, ^{\circ}C$ .
- (3)  $T_{amb} = 25 \, ^{\circ}C$ .

Fig.2 Forward current as a function of forward voltage; typical values.



- (1)  $T_{amb} = 125 \, ^{\circ}C$ .
- (2)  $T_{amb} = 85 \, ^{\circ}C$ .
- (3)  $T_{amb} = 25 \,^{\circ}C$ .

Fig.3 Reverse current as a function of reverse voltage; typical values.



 $f = 1 \text{ MHz}; T_{amb} = 25 \,^{\circ}\text{C}.$ 

Fig.4 Diode capacitance as a function of reverse voltage; typical values.

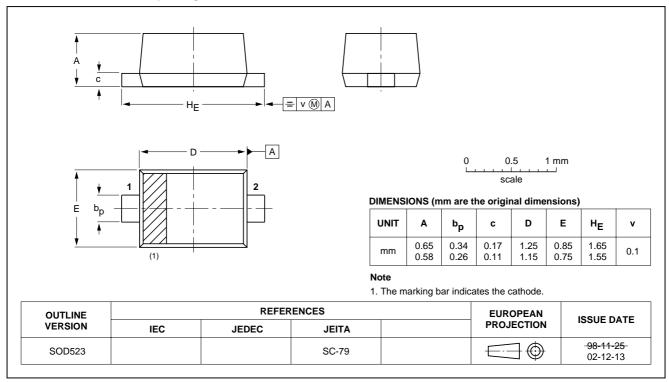
# Low V<sub>F</sub> MEGA Schottky barrier diode

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# **PACKAGE OUTLINE**

# Plastic surface mounted package; 2 leads

**SOD523** 



# Low V<sub>F</sub> MEGA Schottky barrier diode

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### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

### **Notes**

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# **NXP Semiconductors**

### **Customer notification**

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

### **Contact information**

For additional information please visit: http://www.nxp.com
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